

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**LISTING OF CLAIMS:**

1. (Currently Amended) A method for forming a metal film on a non-circuit-formed surface of a semiconductor wafer, the method comprising:  
wherein a metal film is formed by applying an adhesive film to a circuit-formed surface of a semiconductor wafer, the adhesive film comprising an adhesive layer formed on one surface of a base film, the base film comprising at least one film layer having a gas transmission rate of not more than 49.35 ml/m<sup>2</sup>·day/MPa; and [.]  
forming a metal film on the non-circuit-formed surface of the semiconductor wafer to which the adhesive film is applied to a circuit-formed surface of a semiconductor wafer (a non-metal-film-formed surface).
  
2. (Currently Amended) The method for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to claim 1, wherein the film layer having a gas transmission rate of not more than 49.35 ml/m<sup>2</sup>·day/MPa base film comprises a metal film layer or a metal oxide film layer, and at least one film layer having a gas transmission rate of not more than 49.35 ml/m<sup>2</sup>·day/MPa.

3. (Previously Presented) The method for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to claim 1, wherein the base film comprises at least one film layer having a gas transmission rate of not more than  $9.87 \text{ ml/m}^2 \cdot \text{day/MPa}$  and water absorptance of not more than 1.0 weight %.

4. (Previously Presented) The method for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to claim 1, wherein the base film further comprises one film layer selected from an ethylene-vinyl acetate copolymer film, a polyester film and a polyethylene film.

5. (Previously Presented) The method for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to claim 1, wherein the adhesive layer has a storage elastic modulus of not less than  $1 \times 10^5 \text{ Pa}$  at  $150^\circ\text{C}$ .

6. (Previously Presented) An adhesive film for forming a metal film on a non-circuit-formed surface of a semiconductor wafer, comprising an adhesive layer formed on one surface of a base film comprising at least one film layer having a gas transmission rate of not more than  $49.35 \text{ ml/m}^2 \cdot \text{day/MPa}$ .

7. (Previously Presented) An adhesive film for forming a metal film on a non-circuit-formed surface of a semiconductor wafer, comprising an adhesive layer formed on one surface of a base film comprising at least one film layer having a gas

transmission rate of not more than 9.87 ml/m<sup>2</sup>·day/MPa and water absorptance of not more than 1.0 weight %.

8. (Previously Presented) The method for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to claim 2, wherein the base film further comprises one film layer selected from an ethylene-vinyl acetate copolymer film, a polyester film and a polyethylene film.

9. (Previously Presented) The method for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to claim 3, wherein the base film further comprises one film layer selected from an ethylene-vinyl acetate copolymer film, a polyester film and a polyethylene film.

10. (Previously Presented) The method for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to claim 2, wherein the adhesive layer has a storage elastic modulus of not less than  $1 \times 10^5$  Pa at 150°C.

11. (Previously Presented) The method for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to claim 3, wherein the adhesive layer has a storage elastic modulus of not less than  $1 \times 10^5$  Pa at 150°C.

12. (New) The method for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to claim 1, wherein the film layer is the outermost layer of the base film.

13. (New) The method for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to claim 2, wherein the metal film layer or the metal oxide film layer is the outermost layer of the base film at the side the adhesive film is not formed.

14. (New) The adhesive film for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to claim 10, wherein the film layer comprises a metal film layer or a metal oxide film layer.

15. (New) the adhesive film for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to claim 10, wherein the film layer is the outermost layer of the base film.

16. (New) The adhesive film for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to claim 14, wherein the metal film layer or the metal oxide film layer is the outermost layer of the base film at the side the adhesive film is not formed.